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STATEMENT BY APPLICANT				First Named Inventor	Oleg GRUDIN et al.	
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Sheet	1	of	2	Attorney Docket Number	14836-8US-2 AD/mb	

Examiner Initials*	Cite No.1	Document Number Number - Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Unes Where Refevant Passages or Relevan Figures Appear
CON		US-4,472,239	18 Sep. 1984	Robert E. Higashi et al.	
20		US-5,635,893	3 June 1997	Renwin J. Yee et al.	
		US-5,466,484	14 Nov. 1995	Gary L. Spraggins et al.	
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1		US-2002/033519	Mar. 21, 2002	Jeffrey A. Babcock et al.	
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COU		WO03/023794	Mar. 20, 2003	Oleg Grudin et al.				
CON		EP 1 275 967	Jan. 15, 2003	Honeywell Inc.		_		
						 		
	 							

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Sheet	2	of	2	Attorney Docket Number	14836-8US-2 AD/mb	

	NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T²				
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Substitute fo	for form 1449PTO		TO ALL BERNATURE	Complete if Known		
			TIT ALL	Application Number	10/796, 420	
INF	ORMATION	DIS	CLOSURE	Filing Date	March 10, 2004	
STATEMENT BY APPLICANT				First Named Inventor	Oleg GRUDIN et al.	
		•		Art Unit	3742	
(use as many sheets as necessary)				Examiner Name	(unknown)	
Sheet	1	of	3	Attorney Docket Number	14836-8US-2 AD/mb	

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Examiner Cite No.1		Document Number Number – Kind Code ² (# known)	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant			
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\dashv		US-5,635,893	Jun. 3, 1997	Spraggins et al.				
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Examiner Cite		Foreign Patent Document	Publication Date	Name of Patentee or	Pages, Columns, Lines Where Relevant Passages	Г		
Initials*	No.	Country Code3 - Number4 - Kind Code5 (# known)	MM-DD-YYYY	Applicant Of Cited Document	or Relevant Figures Appear			
ON		WO 00/21196	Apr. 13, 2000	Honeywell Inc.				
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Examiner Signature	Tu	HOANG	Date Considered	1/19/06	

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				Application Number	10/796, 420	
INF	ORMATIC	N DIS	CLOSURE	Filing Date	March 10, 2004	
ST#	TEMENT	BY AI	PLICANT	First Named Inventor	Oleg GRUDIN et al.	
"				Art Unit	3742	
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Sheet	2	of	3	Attorney Docket Number	14836-8US-2 AD/mb	

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T²	
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Substitute for form 1449PTO				Complete if Known	
				Application Number	10/796, 420
INFORMATION DISCLOSURE				Filing Date	March 10, 2004
STA	TEMENT	BY A	PPLICANT	First Named Inventor	Oleg GRUDIN et al.
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Sheet	3	of	3	Attorney Docket Number	14836-8US-2 AD/mb

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